

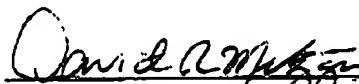
C1
Conold

forming a second porous layer within said first porous layer having a second porosity
higher than said first porosity;
forming at least one semi-conductor film on said surface; and
separating said semi-conductor film from said semi-conductor substrate.--

REMARKS

This amendment adds further related claims 28 and 29 for consideration with this application.

Respectfully submitted,



David R. Metzger (Reg. No. 32,919)
Hill & Simpson
A Professional Corporation
85th Floor - Sears Tower
Chicago, Illinois 60606
Telephone (312) 876-0200 EXT. 3084

ATTORNEYS FOR APPLICANTS